TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12G45, SM12J45, SM12G45A, SM12J45A

AC POWER CONTROL APPLICATIONS

• Repetitive Peak Off-State Voltage: VDRM = 400V, 600V

• R.M.S On-State Current : I_T (RMS) = 12A

• High Commutating (dv / dt)

ABSOLUTE MAXIMUM RATINGS

CHARACTERIS	SYMBOL	RATING	UNIT	
Repetitive Peak	SM12G45 SM12G45A	V_{DRM}	400	
Off-State Voltage	SM12J45 SM12J45A	V DRM	600	
R.M.S On-State Current (Full Sine Waveform Tc = 98°C)		I _{T (RMS)}	12	> A
Peak One Cycle Surge C Current (Non-Repetitive)	I _{TSM}	120 (50Hz) 132 (60Hz)	A	
I ² t Limit Value (t = 1~10ms)		I ² t	72	A^2 s
Critical Rate of Rise of O Current	di / dt	50	A / µs	
Peak Gate Power Dissipa	PGM	5 <	/ w	
Average Gate Power Dis	PG (AV)	0.5	√/w	
Peak Gate Voltage	ХGМ	10	A	
Peak Gate Current	I _{GM}	(3)	\rightarrow_{A}	
Junction Temperature /	\ \ \ \	-40~125))	°C	
Storage Temperature Ra	T _{stg}	-40~125	°C	

Unit: mm

10.3MAX. \$\phi_{3.6 \pm 0.2}\$ \quad \q

Weight: 2.0 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

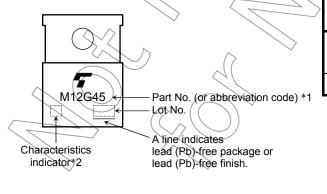
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



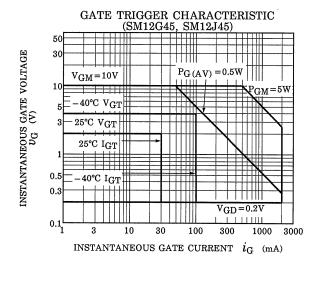
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

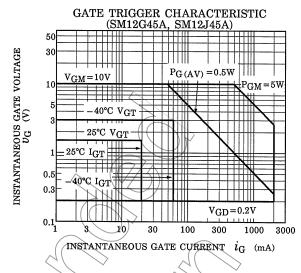
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak	Off-Sta	te Current		I _{DRM}	V _{DRM} =Rated, T _j = 125°C		_	_	2	mA
Gate Trigger Voltage	ı	I			T2 (+) , Gate (+)	_	_	2		
	SM12	//12G45 //12J45	Ш	V _{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (-) <	//	_	2	V
	SM12		Ш			T2 (-) , Gate (-)		_	2	
			IV			T2 (-) , Gate (+)		<u>\</u>	_	
		SM12G45A SM12J45A	-	VGI		T2 (+), Gate (+)) /\		1.5	
			=			T2 (+), Gate (-)	<u> </u>	ı	1.5	
	SM12		Ξ			T2 (-) , Gate (-)	\	ı	1.5	
			IV			T2 (-) , Gate (+)	1	1	_	
		SM12J45	- 1		V _D = 12V, R _L = 20Ω	T2 (+), Gate (+)	1		30	mA
Gate Trigger Current SM			II	lgT		T2 (+) , Gate (-)	- \	47	30	
	SM12		III			T2 (-) , Gate (-)	_	_/	> 30	
			IV			T2 (-) , Gate (+)	\(\)	<u> </u>) —	
		SM12G45A SM12J45A	I			T2 (+) , Gate (+)			20	
			Ш			T2 (+) , Gate (-)			20	
	SM12		III			T2 (-) , Gate (-)	(-)	_	20	
			IV			T2 (-) , Gate (+) <	\ _	_	_	
Peak On-State Voltage		V _{TM}	1 _{TM} = 17A		_	-	1.5	V		
Gate Non-Trigger Voltage V _{GD}		V_{GD}	V _D = Rated, Tc	≠ 125°C	0.2	_	_	V		
Holding Current		(H	V _D = 12V, I _{TM} = 1A		_	_	50	mA		
Thermal Resistance		Junction to Case, AC		_	_	1.8	°C / W			
Critical Rate of Rise of Off-State Voltage at Commutation SM12G45A SM12G45A SM12G45A		((dv / dt) c	V _{DRM} = 400V		10	ı	_	V / µs	
				(dv / dt) C	(di/dt) c = 6.5 A/ms		4			ν / μδ

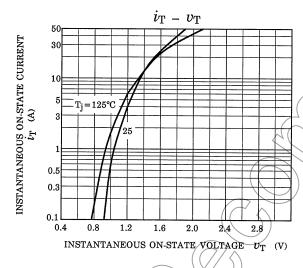
MARKING

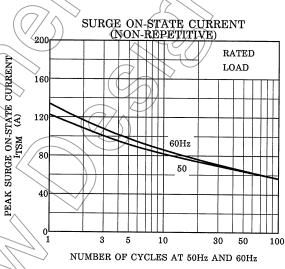


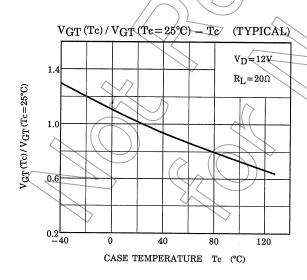
	Part No. (or abbreviation code)	Part No.
*1	M12G45	SM12G45, SM12G45A
	M12J45	SM12J45, SM12J45A
*2	Α	SM12G45A,SM12J45A

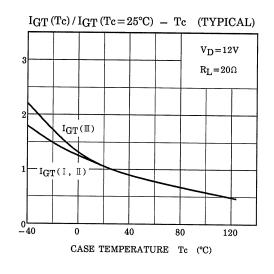




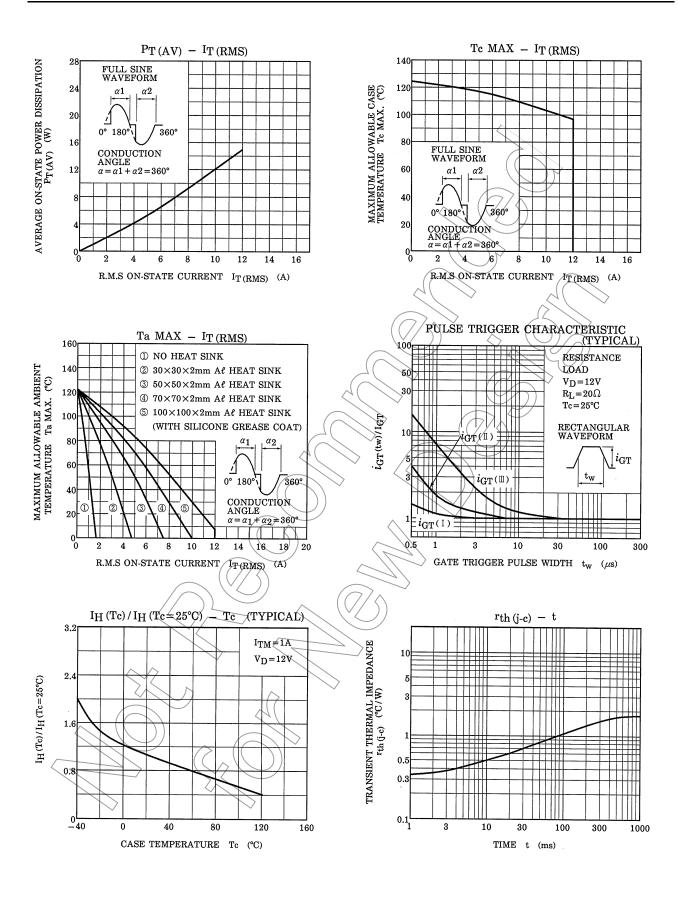








(GT (Tc) / IGT (Tc=25°C)





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2006-10-30